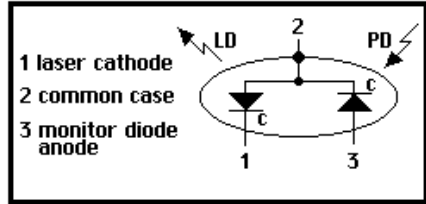


US-Lasers: 780nm-5mW - Infrared Laser Diodes

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INFRARED DIODE LASER DATA SHEETS

ABSOLUTE MAXIMUM RATINGS - (Tc=25 °C)

TECHNICAL DATA • Index Guided MQW Structure • Wavelength: 780nm (Typ.) • Optical Power: 5mW CW • Threshold Current: 25mA (Typ.) • Standard Package: 5.6mm		
Infrared light output	780nm	
Optical power output	5mW CW	
Package Type	5.6mm	
Built-in photo diode for monitoring laser output		
Pin Out Diagram - Style A		

Items	Symbols	Values	Unit
Optical output power	Po	5	mW
Laser diode reverse voltage	VLDR	2	V
Photo diode reverse voltage	VPDR	30	V
Operating temperature	Topr	-10 ~ +40	°C
Storage temperature	Tstg	-40 ~ +85	°C

OPTICAL and ELECTRICAL CHARACTERISTICS - (Tc=25 °C)							
Items	Symbols	Min.	Typ.	Max.	Unit	Test Condition	
Optical output power	Po	-	5	-	mW	-	-
Threshold current	Ith	15	25	40	mA	-	-
Operating current	Iop	25	35	50	mA	Po=5mW	-
Operating voltage	Vop	1.9	2.1	2.5	V	Po=5mW	-
Lasing wavelength	λ D	770	780	790	nm	Po=5mW	-
Beam divergence	θ F	8	11	15	deg	Po=5mW	-
Beam divergence	θ z	20	35	45	deg	Po=5mW	-
Slope Efficiency (mW/mA)	η	0.1	0.3	0.6		-	-
Monitor current	Im	100	200	600	μ A	Po=5mW, Vr=5V	-
Astigmatism	As	-	11	-	μ m	Po=5mW	-
MTTF			3000-5,000 hrs.			Po=5mW, NA=0.4	-
Emitter Size	1 x 4 Microns						
Emitter Distance to Cap Lens	0.3mm						
Structure	Index Guided						